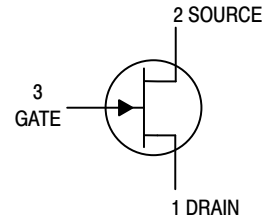


JFET - VHF/UHF Amplifier Transistor

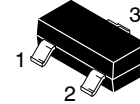
N-Channel

MMBFJ309L, MMBFJ310L, SMMBFJ309L, SMMBFJ310L



Features

- Drain and Source are Interchangeable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



SOT-23 (TO-236)
CASE 318
STYLE 10

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Gate Current	I_G	10	mAdc

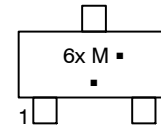
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.

MARKING DIAGRAM



6x = Device Code
x = U for MMBFJ309L, SMMBFJ309L
x = T for MMBFJ310L, SMMBFJ310L

M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBFJ309LT1G, SMMBFJ309LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBFJ310LT1G, SMMBFJ310LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBFJ310LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBFJ309L, MMBFJ310L, SMMBFJ309L, SMMBFJ310L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = -1.0 \mu\text{Adc}$, $V_{DS} = 0$)	$V_{(BR)GSS}$	-25	-	-	Vdc
Gate Reverse Current ($V_{GS} = -15 \text{Vdc}$) ($V_{GS} = -15 \text{Vdc}$, $T_A = 125^\circ\text{C}$)	I_{GSS}	-	-	-1.0 -1.0	nAdc μAdc
Gate Source Cutoff Voltage ($V_{DS} = 10 \text{Vdc}$, $I_D = 1.0 \text{nAdc}$)	$V_{GS(off)}$	-1.0 -2.0	- -	-4.0 -6.5	Vdc
	MMBFJ309 MMBFJ310, SMMBFJ310				
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 10 \text{Vdc}$, $V_{GS} = 0$)	I_{DSS}	12 24	- -	30 60	mAdc
	MMBFJ309 MMBFJ310, SMMBFJ310				
Gate-Source Forward Voltage ($I_G = 1.0 \text{mAdc}$, $V_{DS} = 0$)	$V_{GS(f)}$	-	-	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance ($V_{DS} = 10 \text{Vdc}$, $I_D = 10 \text{mAdc}$, $f = 1.0 \text{kHz}$)	$ Y_{fs} $	8.0	-	18	mmhos
Output Admittance ($V_{DS} = 10 \text{Vdc}$, $I_D = 10 \text{mAdc}$, $f = 1.0 \text{kHz}$)	$ y_{os} $	-	-	250	μmhos
Input Capacitance ($V_{GS} = -10 \text{Vdc}$, $V_{DS} = 0 \text{Vdc}$, $f = 1.0 \text{MHz}$)	C_{iss}	-	-	5.0	pF
Reverse Transfer Capacitance ($V_{GS} = -10 \text{Vdc}$, $V_{DS} = 0 \text{Vdc}$, $f = 1.0 \text{MHz}$)	C_{rss}	-	-	2.5	pF
Equivalent Short-Circuit Input Noise Voltage ($V_{DS} = 10 \text{Vdc}$, $I_D = 10 \text{mAdc}$, $f = 100 \text{Hz}$)	\bar{e}_n	-	10	-	$\text{nV}/\sqrt{\text{Hz}}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

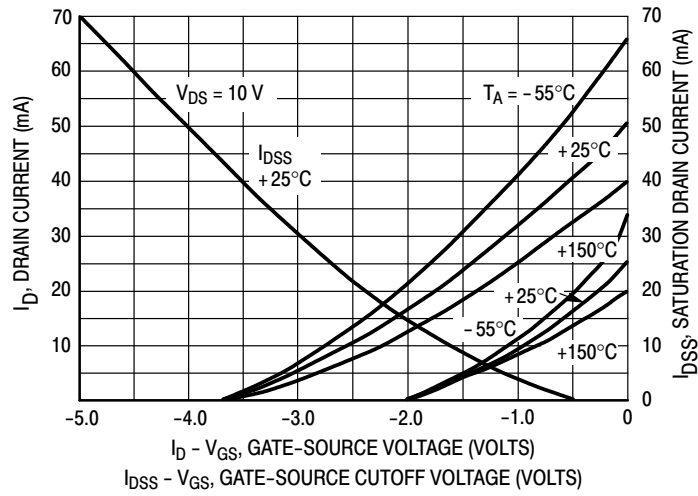


Figure 1. Drain Current and Transfer Characteristics versus Gate-Source Voltage



Figure 2. Common-Source Output Admittance and Forward Transconductance versus Drain Current



Figure 3. On Resistance and Junction Capacitance versus Gate-Source Voltage

MMBFJ309L, MMBFJ310L, SMMBFJ309L, SMMBFJ310L

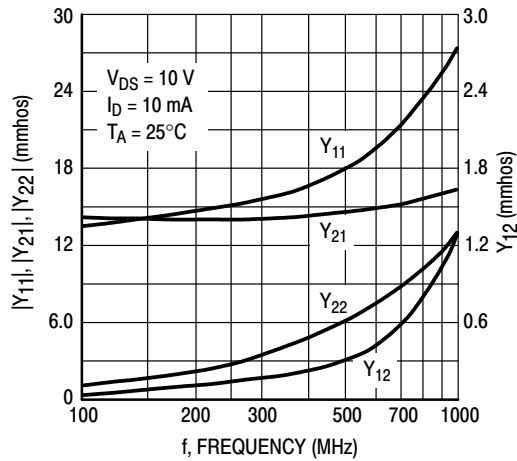


Figure 4. Common-Gate Y Parameter Magnitude versus Frequency

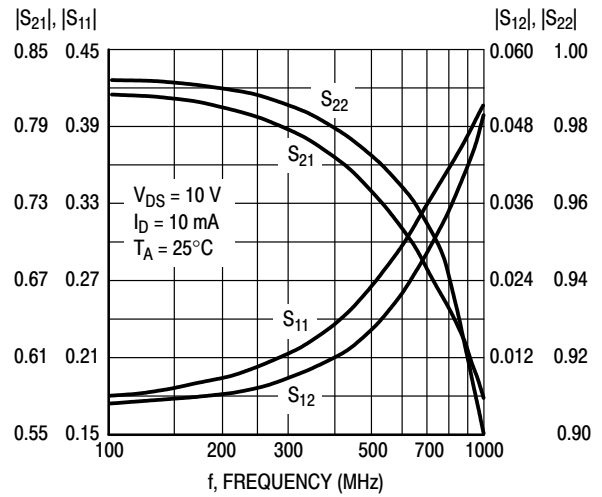


Figure 5. Common-Gate S Parameter Magnitude versus Frequency

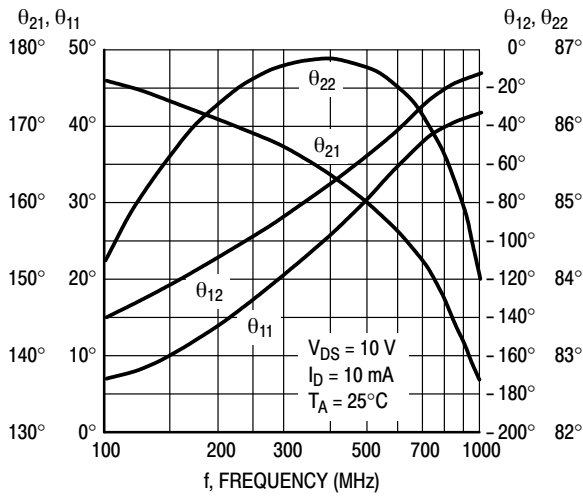


Figure 6. Common-Gate Y Parameter Phase-Angle versus Frequency

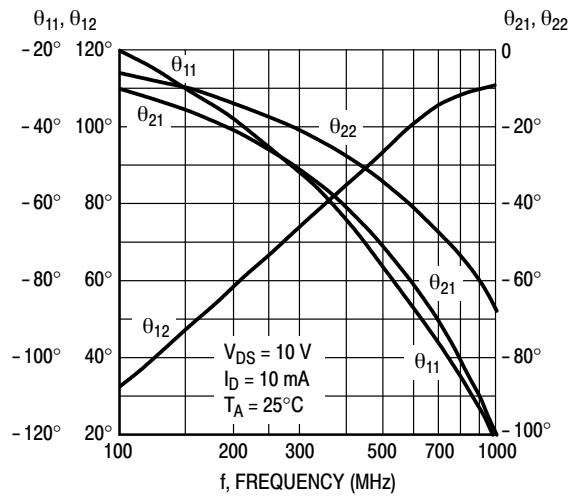


Figure 7. S Parameter Phase-Angle versus Frequency



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
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DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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